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## **GRF2012**

#### Broadband Linear Gain Block 0.05 to 3.8 GHz



#### **Features**

Reference: 5V/90mA/900 MHz

Gain: 14.8 dB

• OIP3: 40.0 dBm

OP1dB: 23.0 dBm

NF: 2.7 dB

Reference: 8V/100mA/900 MHz

Gain: 14.9 dB

OIP3: 40.0 dBm

OP1dB: 25.0 dBm

NF: 2.8 dB

Flexible Bias

• Internally Matched to 50  $\Omega$ 

Process: GaAs pHEMT

#### **Applications**

High Performance Gain Block

Linear Driver Amplifier

Small Cells and Cellular Repeaters

IF Amplifier

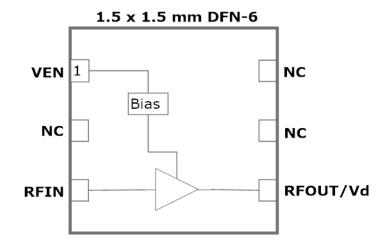
#### **Product Description**

GRF2012 is a broadband gain block with low noise figure and industry leading linearity designed for small cell, wireless infrastructure and other high performance applications. It exhibits outstanding broadband NF, linearity over 700 to 3800 MHz with a single match.

The device is operated from a supply voltage of 2.7 to 8.0 V with a selectable Iddq range of 15 to 100 mA for optimal efficiency and linearity.

GRF2012 is internally matched to 50  $\Omega$  at the input and output ports, needing only external DC blocks and a bias choke on the output.

Consult with the GRF applications engineering team for custom tuning/evaluation board data and device sparameters







## Broadband Linear Gain Block 0.05 to 3.8 GHz

#### **Absolute Ratings:**

Parameter	Symbol	Min.	Max.	Unit
Supply Voltage	V <sub>DD</sub>	0	9.0	V
RF Input Power: (Load VSWR < 2:1; V <sub>D</sub> : <= 8.0 volts)	P <sub>IN MAX</sub>		22	dBm
Operating Temperature (Package Heat Sink)	T <sub>AMB</sub>	-40	105	°C
Maximum Channel Temperature (MTTF > 10^6 Hours)	Тмах		170	°C
Maximum Dissipated Power	P <sub>DISS MAX</sub>		1.0	W
Electrostatic Discharge:				
Charged Device Model:	CDM	1500		V
Human Body Model:	НВМ	250		V
Storage:				
Storage Temperature	T <sub>STG</sub>	-65	150	°C
Moisture Sensitivity Level	MSL		1	



Caution! ESD Sensitive Device



Exceeding Absolute Maximum Rating conditions may cause permanent damage to the device.

Note: For package dimensions and manufacturing information, see the Guerrilla-RF.com website for the following document located on the GRF2012 landing page: Manufacturing Note—MN-001 Product Tape and Reel, Solderability and Package Outline Specification.

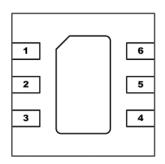
Link to manufacturing note

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#### **Broadband Linear Gain Block** 0.05 to 3.8 GHz

### Pin Out (Top View)



### Pin Assignments:

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Pin	Name	Description	Note
1	Venable	Enable Voltage Input	Venable and series resistor set IDDQ. Venable < =0.2 volts disables device. On -die pull-down resistor will turn the part off if this node is allowed to float.
2	NC	No Connect or Ground	No internal connection to die
3	RF_In	LNA RF input	Internally matched $50\Omega.$ An external DC blocking cap must be used.
4	RF_Out	LNA RF output	Internally matched $50\Omega$ . $V_{DD}$ must be applied through a choke to this pin
5	NC	No Connect or Ground	No internal connection to die
6	NC	No Connect or Ground	No internal connection to die
PKG BASE	GND	Ground	Provides DC and RF ground for LNA, as well as thermal heat sink. Recommend multiple 8 mil vias beneath the package for optimal RF and thermal performance. Refer to evaluation board top layer graphic on schematic page.



# Broadband Linear Gain Block 0.05 to 3.8 GHz

### **Nominal Operating Parameters:**

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Doromotor	Symbol	Specification			Unit	Condition	
Parameter		Min.	Тур.	Max.	Unit	Condition	
Test Frequency	F <sub>TEST</sub>		900		MHz	V <sub>DD</sub> = 5.0 V, T <sub>A</sub> = 25 °C	
Gain	S21	13.8	14.8		dB		
Evaluation Board Noise Figure	NF		2.7		dB		
Output 3rd Order Intercept	OIP3		40.0		dBm	+2.0 dBm P <sub>OUT</sub> per tone at 2 MHz Spacing (899 and 901 MHz)	
Output 1dB Compression Power	OP1dB	21.5	23.0		dBm		
Switching Rise Time	T <sub>RISE</sub>		200		ns		
Switching Fall Time	T <sub>FALL</sub>		300		ns		
Supply Current	I <sub>DD</sub>		90.0		mA		
Enable Current	lenable		5.0		mA		
Disabled Mode							
Leakage Current	ILEAKAGE		110		uA	VDD: 5.0V; VENABLE: 0.0V	
Thermal Data							
Thermal Resistance: (Infra-Red Scan)	Θјс		55		°C/W	On standard Evaluation Board	
Channel Temperature @ +85 C Reference (Package heat sink)	TCHANNEL		110		°C	V <sub>DD</sub> : 5.0 V; I <sub>DDQ</sub> : 90 mA; No RF; P <sub>DISS</sub> : 450 mW	



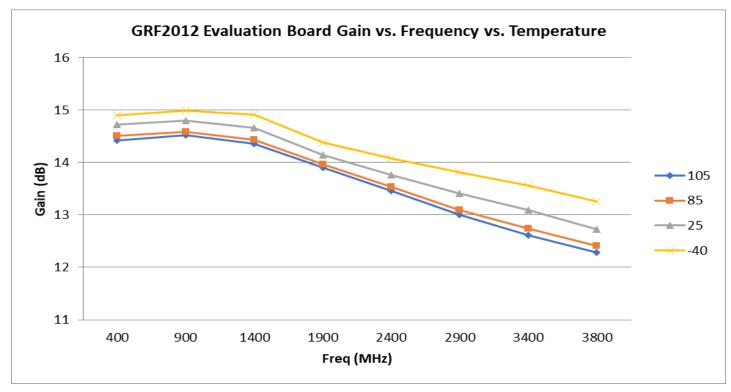


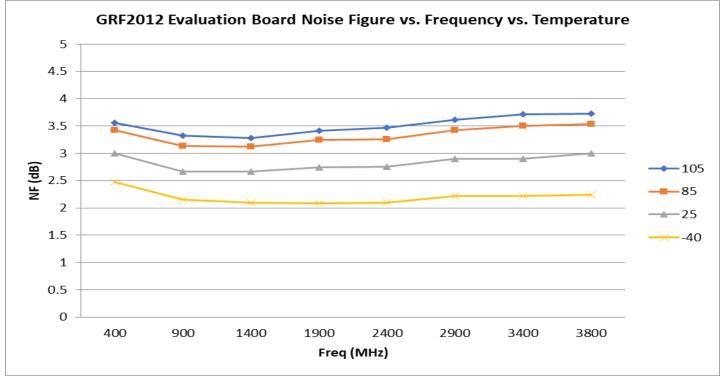
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## Broadband Linear Gain Block 0.05 to 3.8 GHz

#### **GRF2012** Evaluation Board Measured Data vs. Bias: (0.4 to 3.8 GHz Tune)







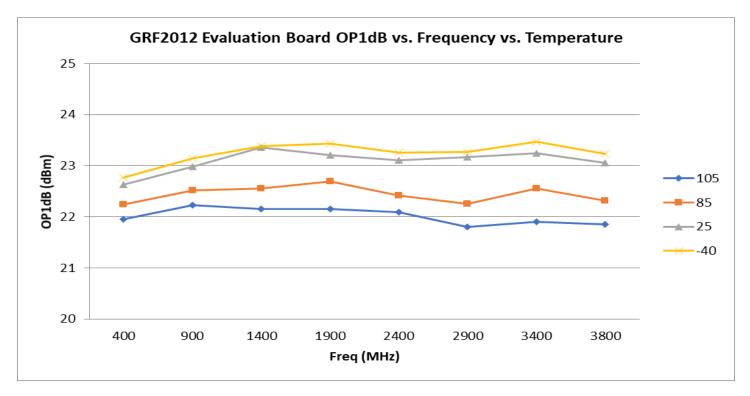


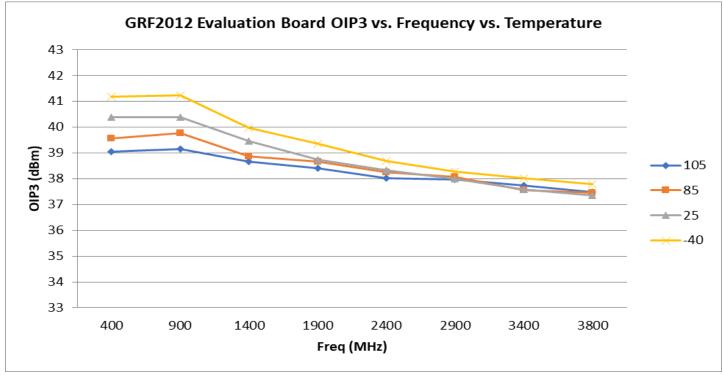
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# Broadband Linear Gain Block 0.05 to 3.8 GHz

#### **GRF2012** Evaluation Board Measured Data vs. Bias: (0.4 to 3.8 GHz Tune)





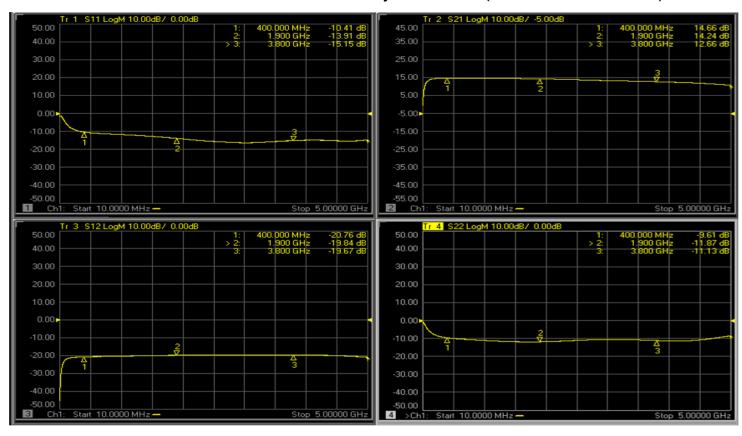


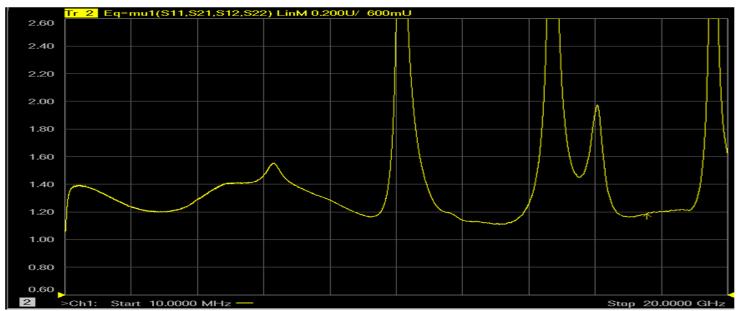


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## Broadband Linear Gain Block 0.05 to 3.8 GHz

#### GRF2012 Evaluation Board S-Pars and Stability Mu Factor: (0.4 to 3.8 GHz Match)

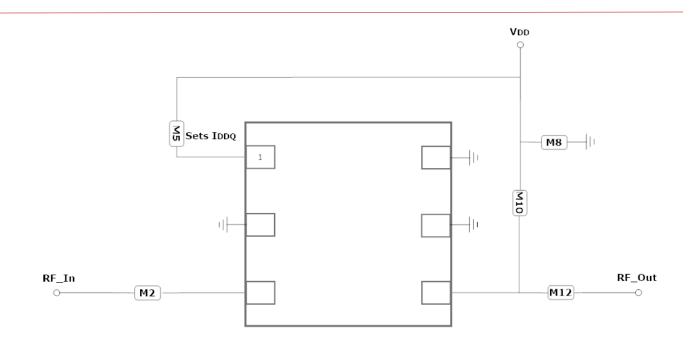




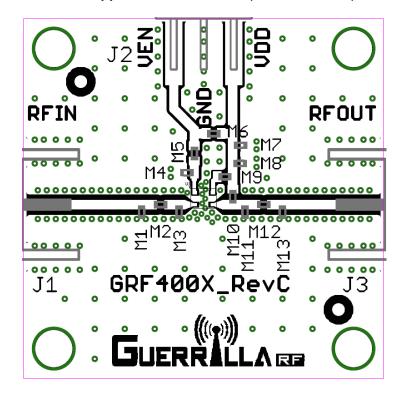
Note: Mu factor >= 1.0 implies unconditional stability.



# Broadband Linear Gain Block 0.05 to 3.8 GHz



#### **GRF2012** Application Schematic (0.7 to 3.8 GHz)



**GRF2012 Evaluation Board Assembly Diagram** 





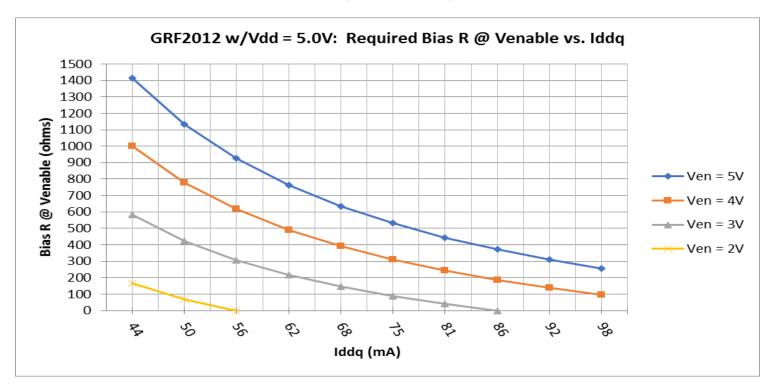
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#### **Broadband Linear Gain Block** 0.05 to 3.8 GHz

#### **GRF2012 Standard Evaluation Board BOM: (0.7 to 3.8 GHz Tune)**

Component	Туре	Manufacturer	Family	Value	Package Size	Substitution
M2	Capacitor	Murata	GRM	100 pF	0402	ok
M5 (See curves)	Resistor	Various	5%	Sets Iddq	0402	ok
M8	Capacitor	Murata	GRM	0.1 uF	0402	ok
M10	Inductor	Murata	LQG	47 nH	0402	ok
M12	Capacitor	Murata	GRM	1000 pF	0402	ok
Evaluation Board	GRF400X_RevC					

Note: Standard evaluation board bias: Vdd: 5.0V; Venable: 5.0V; M5:





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Data Sheet Release Status:	Notes
Advance	S-parameter and NF data based on EM simulations for the fully packaged device using foundry supplied transistor s-parameters. Linearity estimates based on device size, bias condition and experience with related devices.
Preliminary	All data based on evaluation board measurements in the Guerrilla RF Applications Lab.
Released	All data based on device qualification data. Typically, this data is nearly identical to the data found in the preliminary version. Max and min values for key RF parameters are included.

Information in this datasheet is specific to the Guerrilla RF, Inc. ("Guerrilla RF") product identified.

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